

RB751S-40 / RB751V-40

Diodes

Schottky barrier diode

RB751S-40 / RB751V-40

●Applications

High speed switching
For Detection

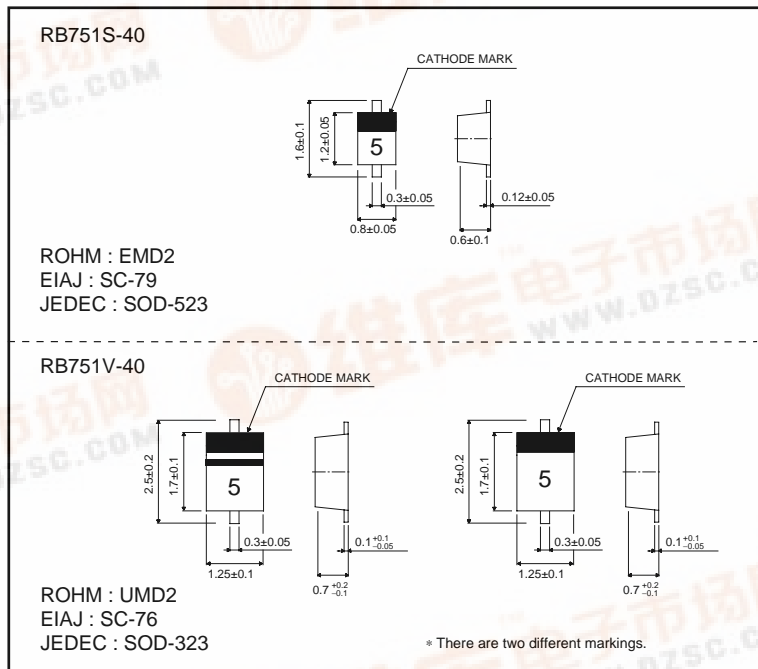
●Features

- 1) Small surface mounting type.
(EMD2, UMD2)
- 2) Low reverse current and low forward voltage.
- 3) High reliability.

●Construction

Silicon epitaxial planar

●External dimensions (Units : mm)



●Absolute maximum ratings (Ta = 25°C)

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V _{RM}	40	V
DC reverse voltage	V _R	30	V
Mean rectifying current	I _o	30	mA
Peak forward surge current*	I _{FSM}	200	mA
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-40~+125	°C

* 60 Hz for 1 μ s

●Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V _F	-	-	0.37	V	I _F = 1mA
Reverse current	I _R	-	-	0.5	μA	V _R = 30V
Capacitance between terminals	C _T	-	2.0	-	pF	V _R = 1V, f = 1MHz

Note) ESD sensitive product handling required.

Diodes

●Electrical characteristic curves (Ta = 25°C)

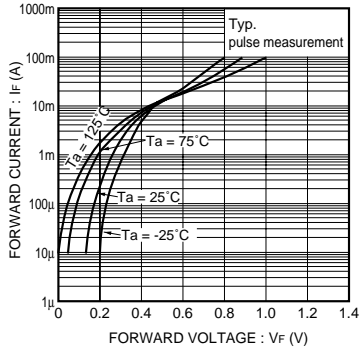


Fig. 1 Forward characteristics

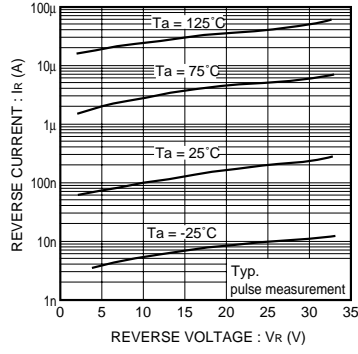


Fig. 2 Reverse characteristics

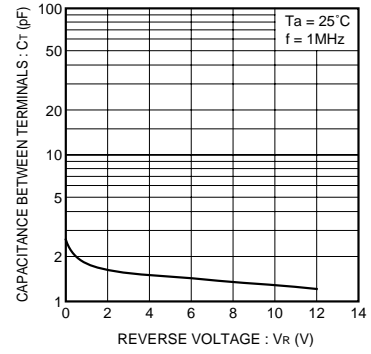


Fig. 3 Capacitance between terminals characteristics